## Shaharin Fadzli Abd Rahman

List of Publications by Year in descending order

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1307594 1372567 21 127 10 7 citations g-index h-index papers 21 21 21 161 docs citations times ranked citing authors all docs

#	Article	IF	Citations
1	Gaussian distribution of inhomogeneous barrier height in nanocrystalline graphite (NCG)/p-Si Schottky diodes. Japanese Journal of Applied Physics, 2019, 58, 065002.	1.5	О
2	Investigation on Transition Diode Properties of rGOâ€GO/nâ€Si Heterojunction. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900064.	1.8	11
3	Junction properties analysis of silicon back-to-back Schottky diode with reduced graphene oxide Schottky electrodes. Microelectronic Engineering, 2018, 196, 32-37.	2.4	24
4	Fabrication of reduced graphene oxide-gated AlGaAs/GaAs heterojunction transistor., 2016,,.		0
5	Defect-free mixed mono- and bi-layer graphene synthesized from refined palm oil by thermal chemical vapor deposition. Materials Letters, 2016, 182, 168-172.	2.6	14
6	Graphene as a Buffer Layer for Silicon Carbide-on-Insulator Structures. Materials, 2012, 5, 2270-2279.	2.9	9
7	Room temperature nonlinear operation of a graphene-based three-branch nanojunction device with chemical doping. Applied Physics Letters, 2012, 100, .	3.3	22
8	Fabrication and transport performance of three-branch junction graphene nanostructure. , 2012, , .		0
9	Graphene layer number determination from red-, green-, and blue-channel of optical images. , 2012, , .		O
10	Identification of Graphene Layer Numbers from Color Combination Contrast Image for Wide-Area Characterization. Japanese Journal of Applied Physics, 2012, 51, 06FD09.	1.5	5
11	Fabrication and Characterization of Planar Dipole Antenna Integrated with GaAs Based-Schottky Diode for On-chip Electronic Device Application. IOP Conference Series: Materials Science and Engineering, 2011, 17, 012023.	0.6	1
12	Dual-Functional On-Chip AlGaAs/GaAs Schottky Diode for RF Power Detection and Low-Power Rectenna Applications. Sensors, 2011, 11, 8127-8142.	3.8	15
13	Power Conversion Efficiency of AlGaAsâ <sup>•</sup> GaAs Schottky Diode for Low-Power On-Chip Rectenna Device Application., 2011,,.		О
14	RF–DC power conversion of Schottky diode fabricated on AlGaAs/GaAs heterostructure for on-chip rectenna device application in nanosystems. Microsystem Technologies, 2010, 16, 1713-1717.	2.0	6
15	Design, fabrication and characterization of a Schottky diode on an AlGaAs/GaAs HEMT structure for on-chip RF power detection. Superlattices and Microstructures, 2010, 47, 274-287.	3.1	12
16	Effects of various metal contacts on contact resistance and barrier height of metal/graphene interface. , $2010$ , , .		0
17	RF characterization of planar dipole antenna for on-chip integration with GaAs-based schottky diode. , 2009, , .		3
18	RF-DC power conversion of Schottky diode fabricated on AlGaAs/GaAs heterostructure for on-chip rectenna device application in nanosystem. , 2009, , .		2

#	Article	IF	CITATIONS
19	Fabrication of open gate structure on GaN-based HEMT for pH sensing. , 2009, , .		2
20	On-chip integration of planar dipole antenna with AlGaAs/GaAs Schottky diode for RF power detection. , 2009, , .		0
21	Dry Transfer Process of Single-Layer Graphene on Multi-Layer Hexagonal Boron Nitride for High Quality Heterostructure. Materials Science Forum, 0, 1055, 171-178.	0.3	1